

Please amend the subject application as follows:

**IN THE SPECIFICATION**

Please amend the paragraph beginning at page 1, line 9 and ending at page 1, line 17 as follows:

--A thin film transistor (TFT) array panel is utilized for driving pixels of a display device such as a liquid crystal display (LCD) or an organic electroluminescence (EL) display device. The TFT array panel includes a plurality of gate lines transmitting scanning signals, a plurality of data lines transmitting data signals, a plurality of TFTs connected to the gate lines and the data lines, a plurality of pixel electrode connected to the TFTs, a gate insulating layer covering the gate lines, and a passivation layer covering the data lines. The TFT array panel selectively transmits the data signals to the pixel electrodes in response to the scanning signals. The TFT includes a semiconductor layer made of amorphous silicon or polysilicon.--

Please amend the paragraph beginning at page 5, line 12 and ending at page 5, line 17 as follows:

--A plurality of gate lines 121 for transmitting gate signals and a gate shorting bar [[124]] extending substantially in a longitudinal direction are formed on an insulating substrate 110. Each gate line 121 extends substantially in a transverse direction and a plurality of portions of each gate line 121 form a plurality of gate electrodes 123. Each gate line 121 includes a plurality of projections protruding

downward and it may have an expansion having wider width for contact with another layer or an external device.--

Please amend the paragraph beginning at page 6, line 10 and ending at page 6, line 14 as follows:

--A plurality of semiconductor islands 154 preferably made of polysilicon are formed on the gate insulating layer 140 opposite the gate electrodes 123. Each semiconductor island ~~[[151]]~~ 154 includes a pair of ohmic contact areas 163 and 165 doped with n type or p type impurity such as boron (B) and phosphorous (P) at the top surfaces and are separated from each other.--

Please amend the paragraph beginning at page 7, line 16 and ending at page 7, line 20 as follows:

--The ohmic contact areas 163 and 165 reduce the contact resistance between the underlying semiconductor islands ~~[[151]]~~ 154 and the overlying data lines 171 and the overlying drain electrodes 175. The semiconductor ~~[[stripes 151]]~~ islands 154 include a plurality of exposed portions, which are not covered with the data lines 171 and the drain electrodes 175, such as portions located between the source electrodes 173 and the drain electrodes 175.--

Please amend the paragraphs beginning at page 8, line 4 and ending at page 8, line 11 as follows:

--The passivation layer 180 has a plurality of contact holes 181 and 182 exposing the drain electrodes 175 and the storage conductors 177. The passivation layer 180 may further ~~[[has]]~~ have a plurality of contact holes (not shown) exposing the expansions of the data lines 171. The passivation layer 180 and the gate insulating layer 140 may have a plurality of contact holes (not shown) exposing the expansions of the gate lines 121.

A plurality of pixel electrodes ~~[[191]]~~ 190 and, preferably, a plurality of contact assistants (not shown), which are preferably made of ITO or IZO, are formed on the passivation layer 180.--

Please amend the paragraph beginning at page 9, line 14 and ending at page 9, line 16 as follows:

--A method of manufacturing the TFT array panel shown in Figs. ~~[[1-4]]~~ 1A and 1B according to an embodiment of the present invention will be now described in detail with reference to Figs. 2A to 8B as well as Figs. 1A and 1B.--

Please amend the paragraph beginning at page 10, line 15 and ending at page 11, line 2 as follows:

--The position-dependent thickness of the photoresist is obtained by several techniques, for example, by providing translucent areas on the exposure mask ~~[[300]]~~ as well as transparent areas and light blocking opaque areas. The translucent areas

may have a slit pattern, a lattice pattern, a thin film(s) with intermediate transmittance or intermediate thickness. When using a slit pattern, it is preferable that the width of the slits or the distance between the slits is smaller than the resolution of a light exposer used for the photolithography. Another example is to use reflowable photoresist. In detail, once a photoresist pattern made of a reflowable material is formed by using a normal exposure mask only with transparent areas and opaque areas, it is subject to reflow process to flow onto areas without the photoresist, thereby forming thin portions.—